# MJE15034 (NPN), MJE15035 (PNP)

# **Complementary Silicon Plastic Power Transistors**

### TO-220, NPN & PNP Devices

Complementary silicon plastic power transistors are designed for use as high-frequency drivers in audio amplifiers.

#### **Features**

- High Current Gain Bandwidth Product
- TO-220 Compact Package
- Epoxy meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	350	Vdc
Collector-Base Voltage	V <sub>CB</sub>	350	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	4.0	Adc
Collector Current – Peak	I <sub>CM</sub>	8.0	Adc
Base Current	Ι <sub>Β</sub>	1.0	Adc
Total Power Dissipation  @ T <sub>C</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	50 0.40	W W/°C
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.0 0.016	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

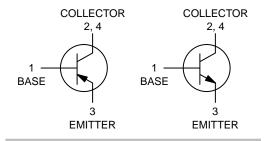


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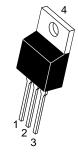
www.onsemi.com

# 4.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 350 VOLTS, 50 WATTS

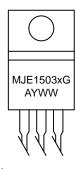
#### **COMPLEMENTARY**



#### MARKING DIAGRAM



TO-220 CASE 221A STYLE 1



MJE1503x = Device Code

x = 4 or 5

= Location Code

= Year

WW = Work Week
G = Pb-Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping
MJE15034G	TO-220 (Pb-Free)	50 Units / Rail
MJE15035G	TO-220 (Pb-Free)	50 Units / Rail

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## MJE15034 (NPN), MJE15035 (PNP)

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 1)	$(I_C = 10 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	350	_	Vdc
Collector Cutoff Current	$(V_{CB} = 350 \text{ Vdc}, I_{E} = 0)$	I <sub>CBO</sub>	-	10	μAdc
Emitter Cutoff Current	$(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	I <sub>EBO</sub>	-	10	μAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain	$ \begin{aligned} &(I_C = 0.1 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_C = 0.5 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_C = 1.0 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_C = 2.0 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \end{aligned} $	h <sub>FE</sub>	100 100 50 10	- - -	-
Collector–Emitter Saturation Voltage	$(I_C = 1.0 \text{ Adc}, I_B = 0.1 \text{ Adc})$	V <sub>CE(sat)</sub>	-	0.5	Vdc
Base-Emitter On Voltage	$(I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$	V <sub>BE(on)</sub>	-	1.0	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain – Bandwidth Product (Note 2) (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)		f⊤	30	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 1. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.
- 2.  $f_T = |h_{fe}| \cdot f_{test}$ .

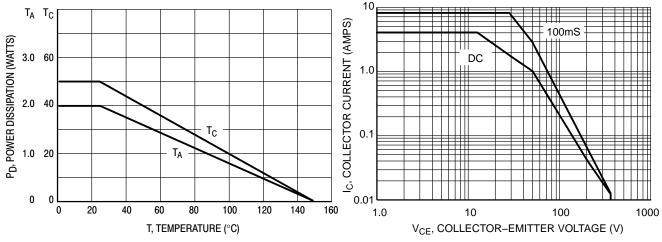


Figure 1. Power Derating

Figure 2. Active Region Safe Operating Area

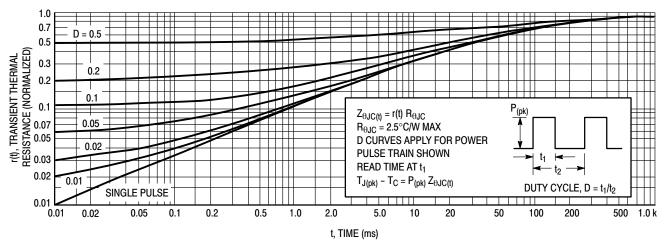


Figure 3. Thermal Response

#### MJE15034 (NPN), MJE15035 (PNP)

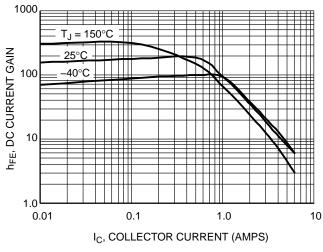


Figure 4. DC Current Gain, V<sub>CE</sub> = 5.0 V NPN MJE15034

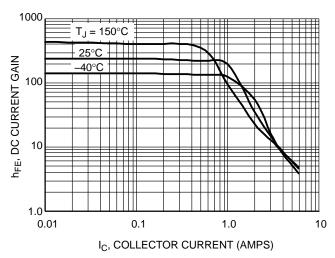


Figure 5. DC Current Gain, V<sub>CE</sub> = 5.0 V PNP MJE15035

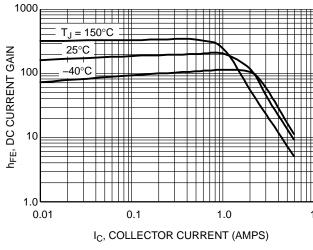


Figure 6. DC Current Gain, V<sub>CE</sub> = 20 V NPN MJE15034

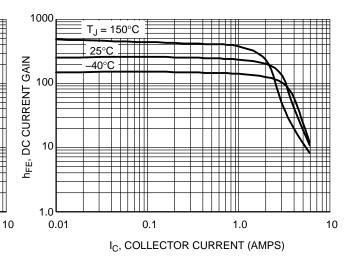


Figure 7. DC Current Gain, V<sub>CE</sub> = 20 V PNP MJE15035

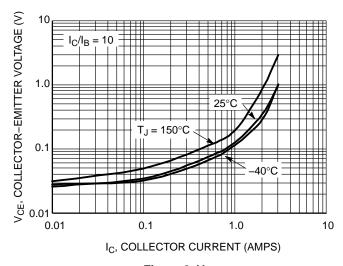


Figure 8. V<sub>CE(sat)</sub> NPN MJE15034

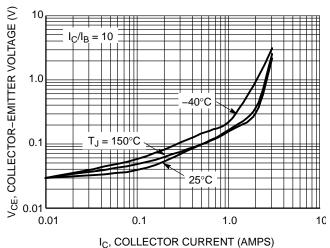


Figure 9. V<sub>CE(sat)</sub> PNP MJE15035

#### MJE15034 (NPN), MJE15035 (PNP)

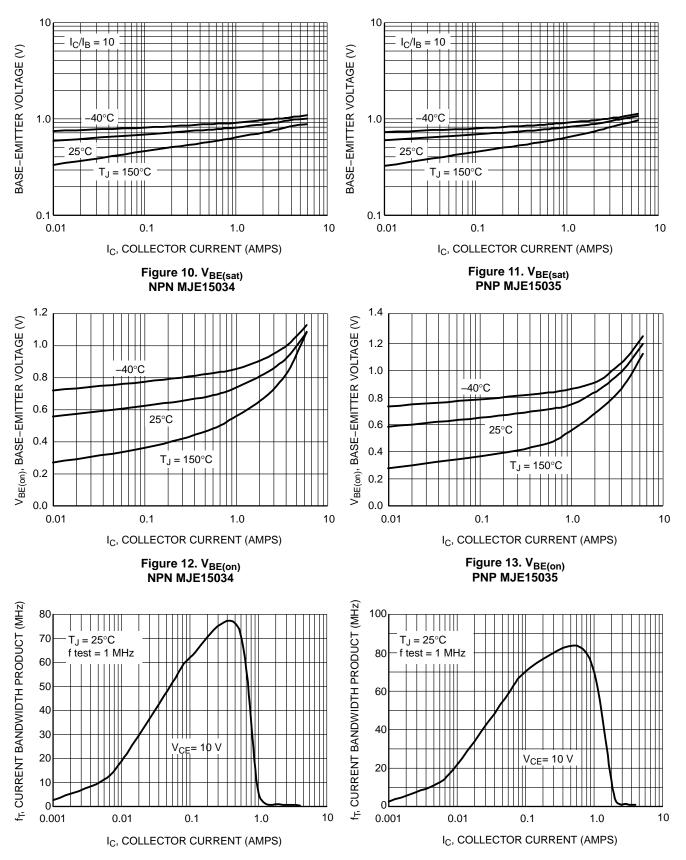
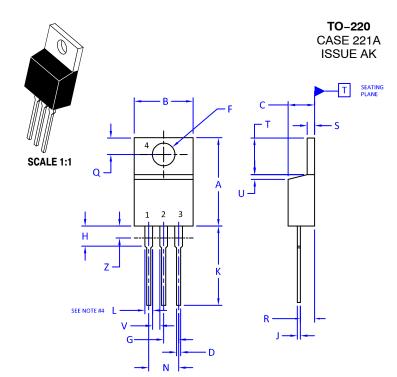


Figure 14. Typical Current Gain Bandwidth Product NPN MJE15034

Figure 15. Typical Current Gain Bandwidth Product PNP MJE15035





**DATE 13 JAN 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

#### 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMI	ETERS
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	2. 3.	ANODE CATHODE ANODE CATHODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.		STYLE 10: PIN 1. 2. 3. 4.	GATE	STYLE 11: PIN 1. 2. 3. 4.	DRAIN	STYLE 12: PIN 1. 2. 3. 4.	

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